



Manufacturability and Computability at the Nano-Scale

Frontiers of Extreme Computing

Stan Williams
October 25, 2005

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"The purpose of QSR is to perform
fundamental research in physical science
with a strategic intent for hp
– to create new technologies that will be
important to the company on a
10+ year time frame."

Discover + Invent





For a more detailed discussion of this work, see

Applied Physics A **80**, March 2005

“Nanoelectronics” Special Issue

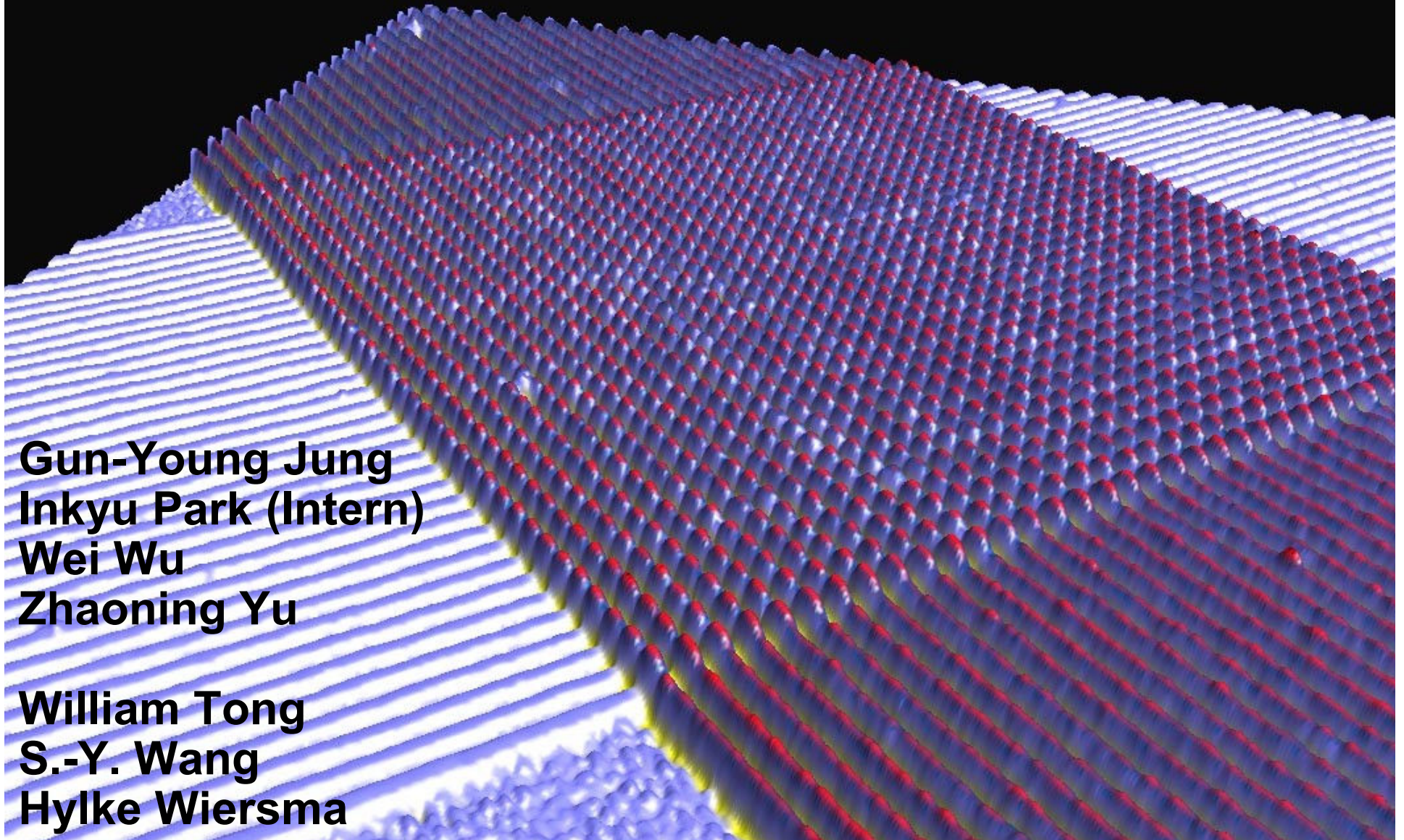
Journal of Applied Physics 97, #034301 (2005)

2005 WSJ Technology Innovation Award

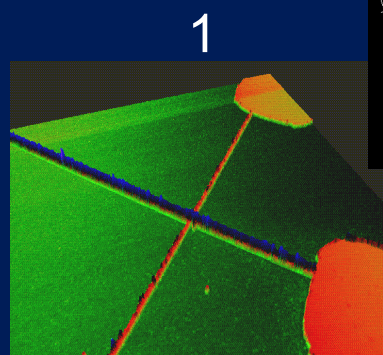
Fabrication by Nanoimprint

Gun-Young Jung
Inkyu Park (Intern)
Wei Wu
Zhaoning Yu

William Tong
S.-Y. Wang
Hylke Wiersma

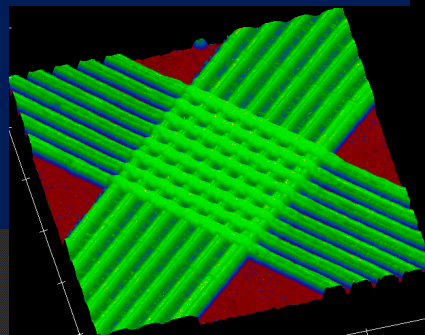


QSR Hyper Moore's Law Progress



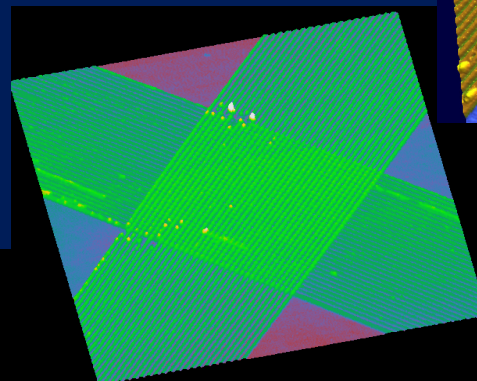
1

2002



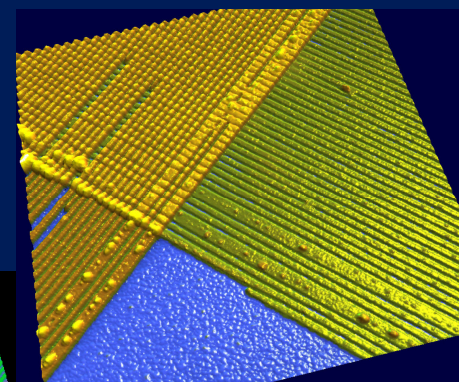
64

2003



1 k

2004



16 k

2005

Lithography Red Brick Wall - 2010



QSR > 13 years ahead!

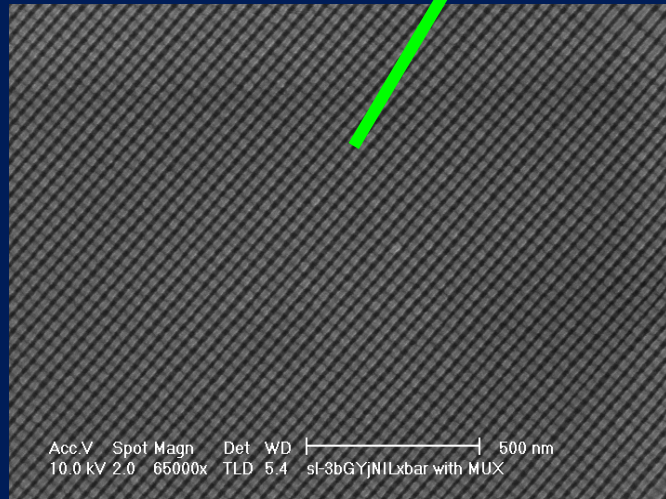
International Technology Roadmap for Semiconductors 2004

year	04	05	06	07	08	09	10	11	12	13	14	15	16	17	18
DRAM ½ pitch nm	90	80	70	65	57	50	45	40	35	32	28	25	22	20	18

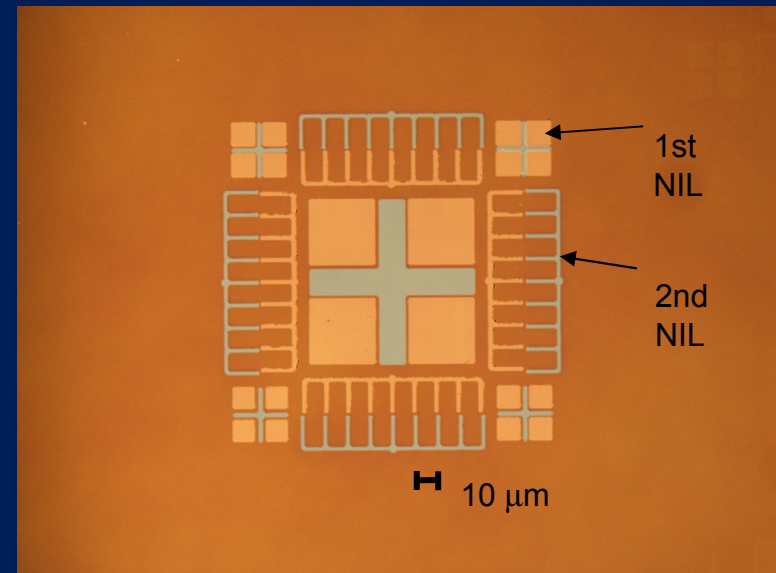
30 nm
→||←



17 nm



G4 nanoimprinter: Total cost \$300k



Wei Wu

- Much more cost-effective than any commercial nanoimprinter
- 0.5 μm alignment accuracy demonstrated
- Targeting 10 nm alignment accuracy (with J. Gao & C. Picciotto)
- Step & repeat compatible design

Architecture

Phil Kuekes

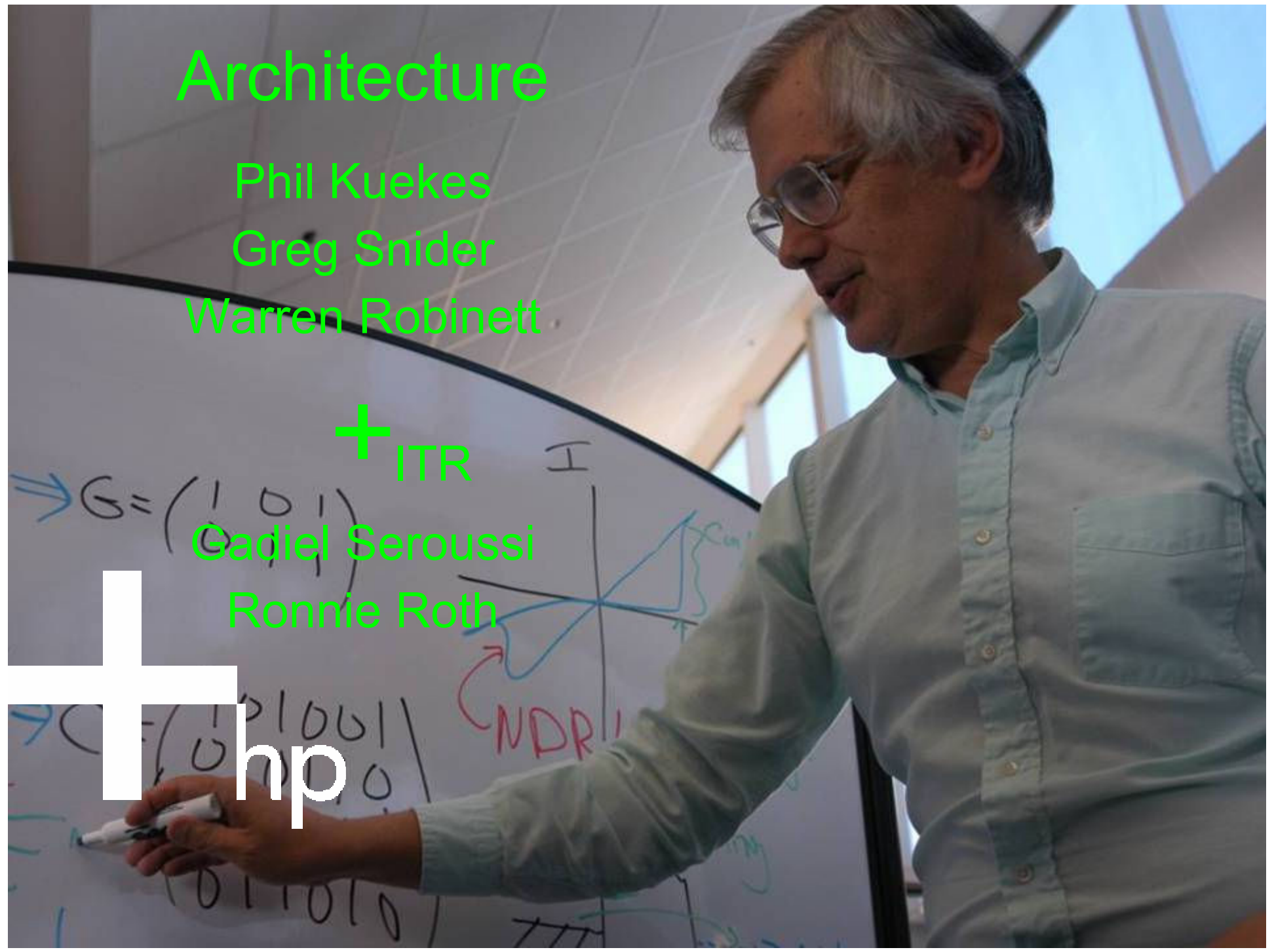
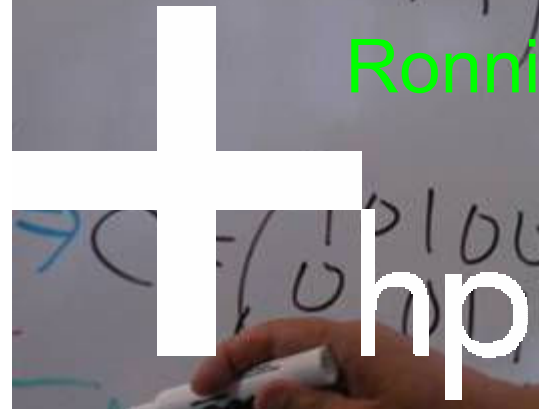
Greg Snider

Warren Robinett

+ ITR

Gadiel Seroussi

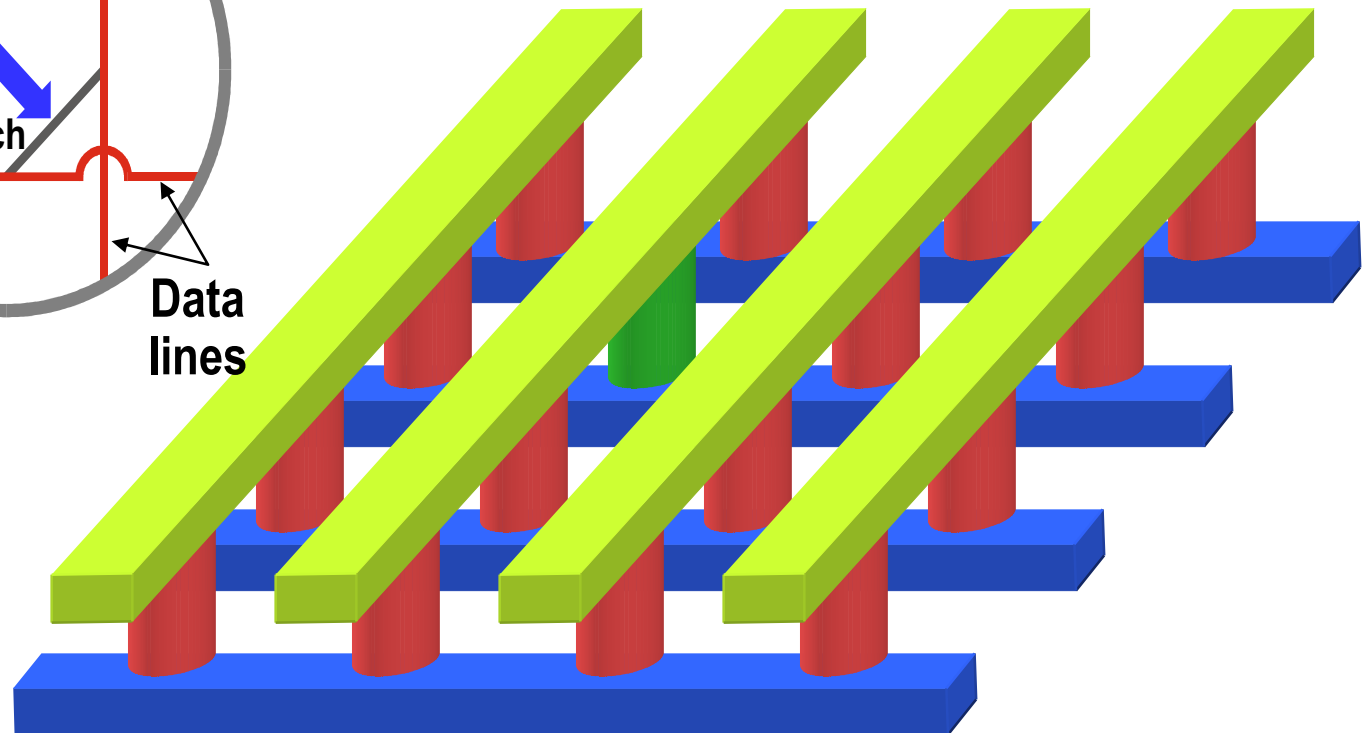
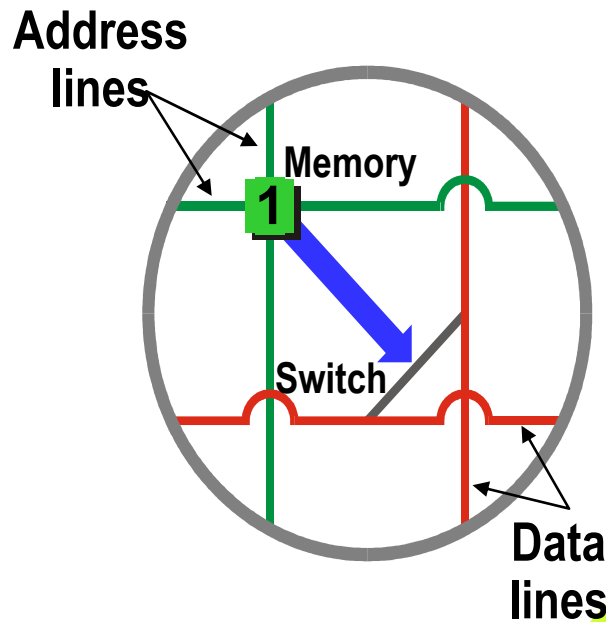
Ronnie Roth



Tunneling-Switch

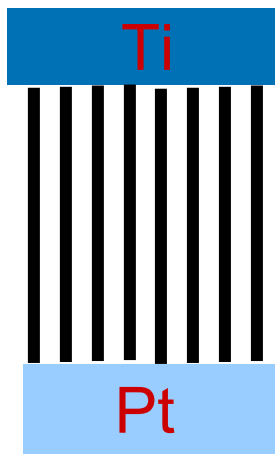
Crossbar Circuits

US Patents 6128214, 6256767, 6314019



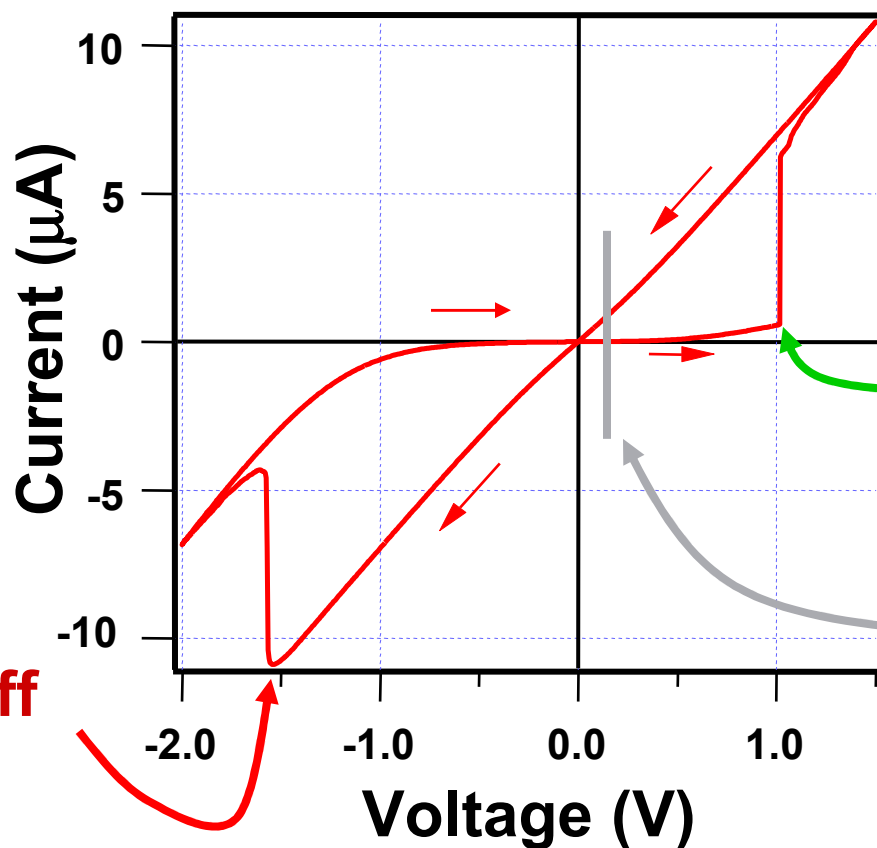
Abstraction of a Field-Programmable Gate Array

Switchable Tunneling Resistor



Device =
Molecule
+ Electrodes

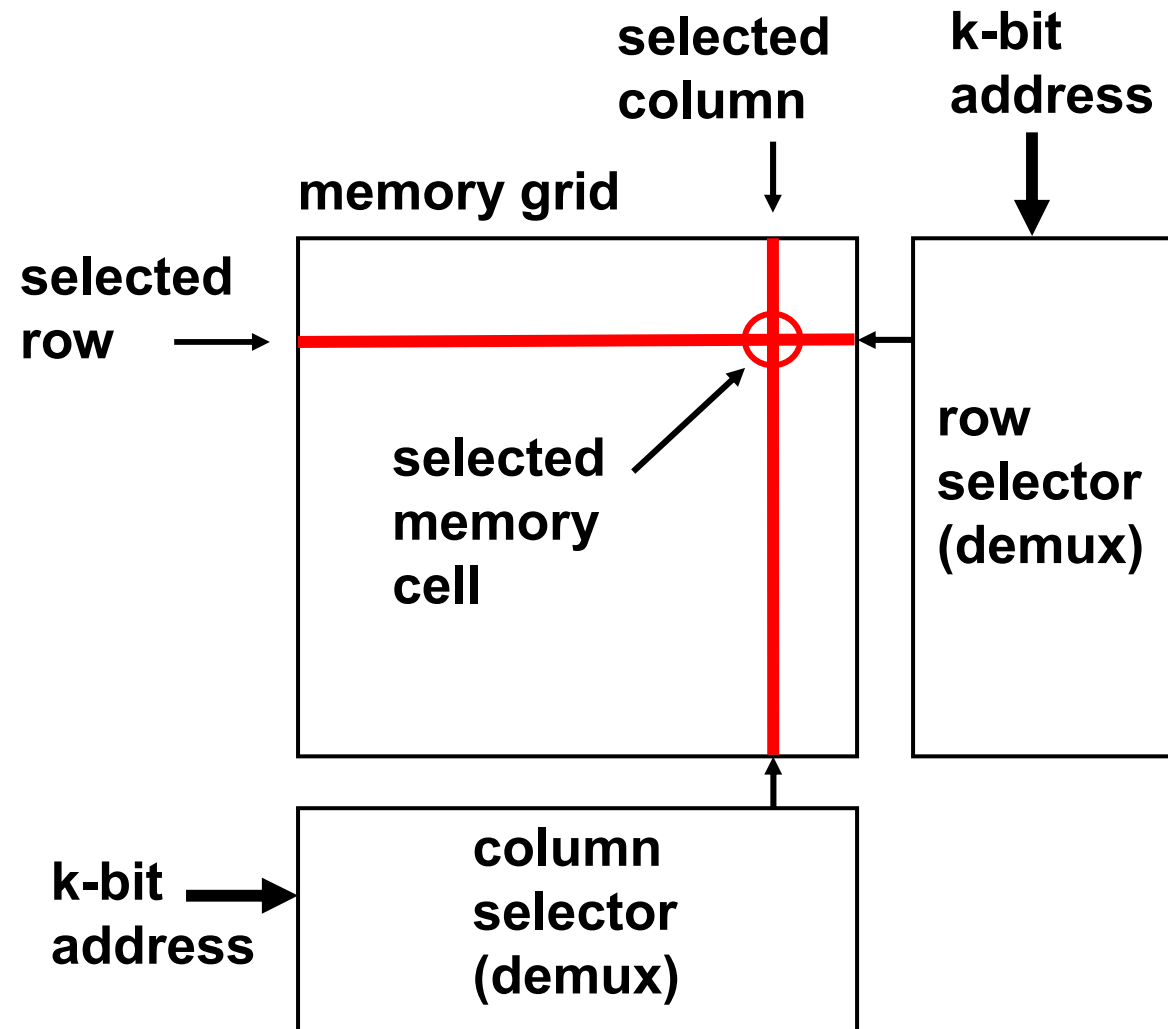
Switch off
"0"



Switch on
"1"

Read bit
(measure
resistance)

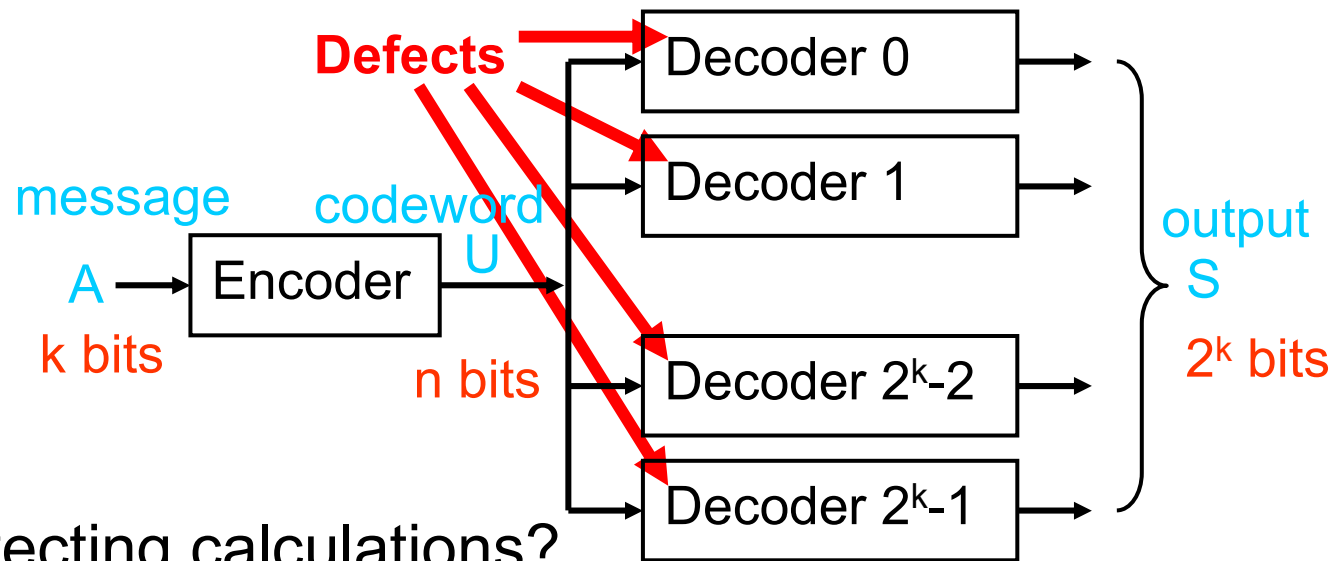
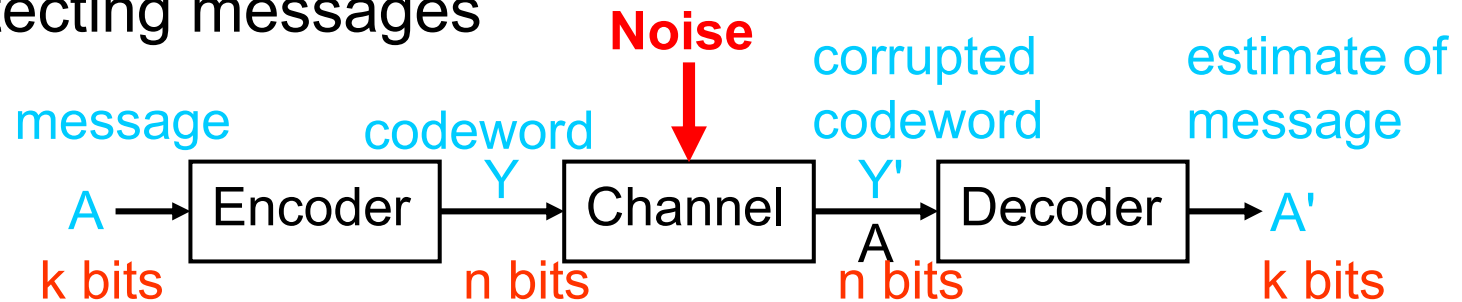
Communicate with the nanowires



Use coding theory to design circuits!

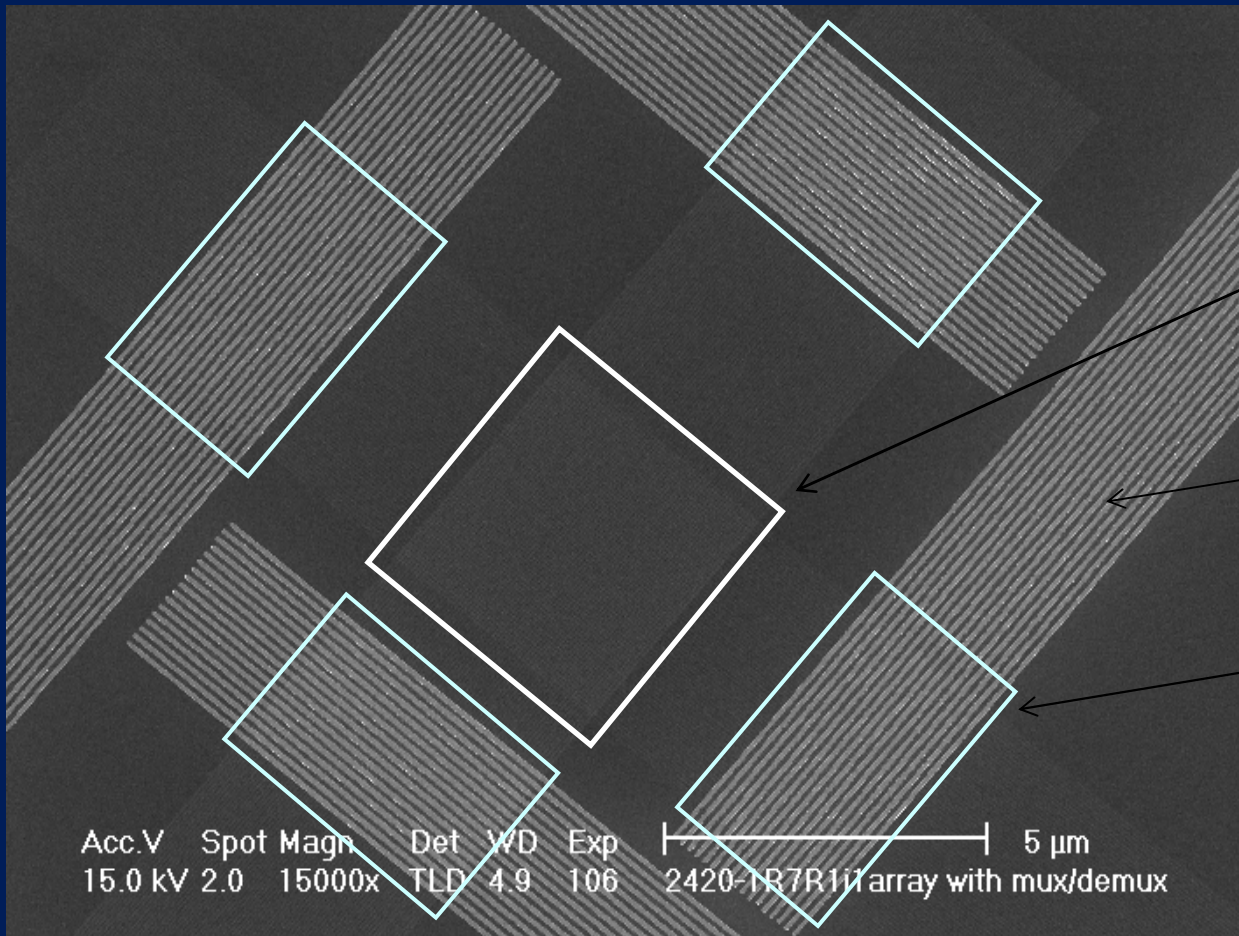


Protecting messages



Protecting calculations?

Four kbit Cross Bar Memory with Mux/Demux



66x66 cross bar memory @30 nm half-pitch

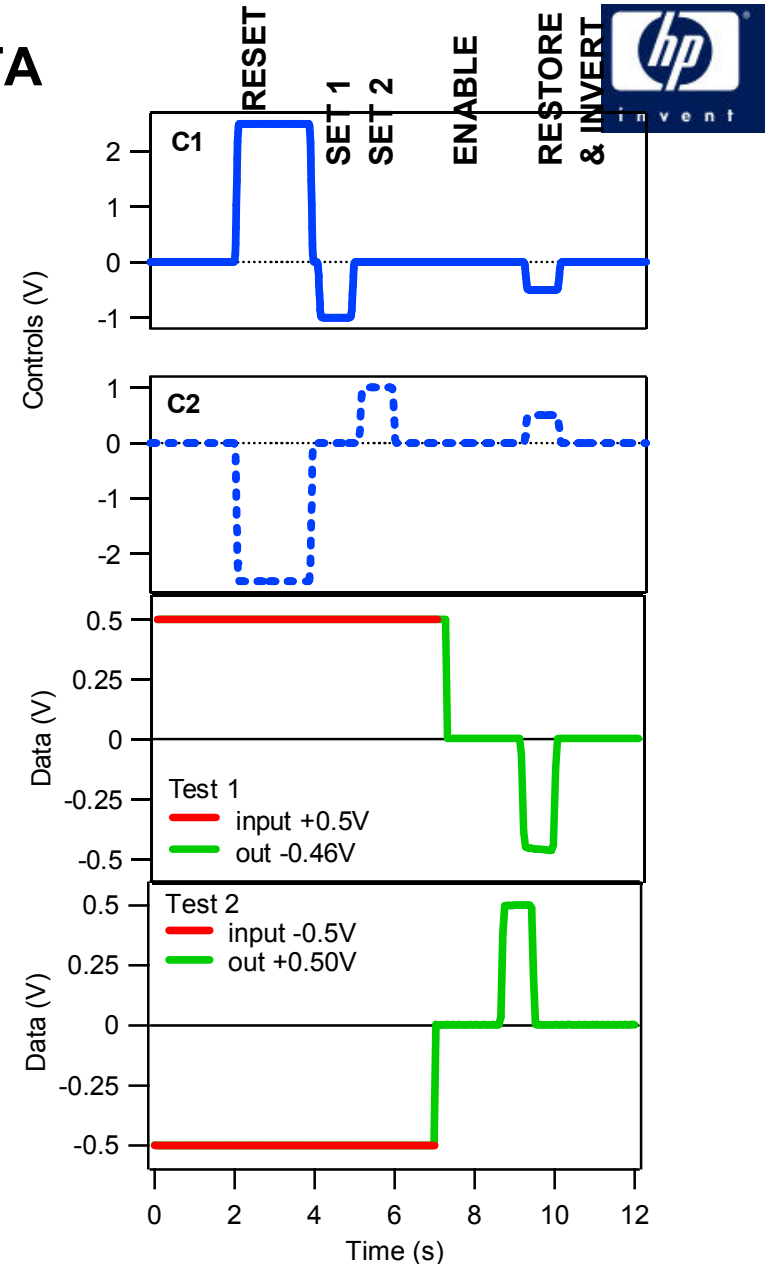
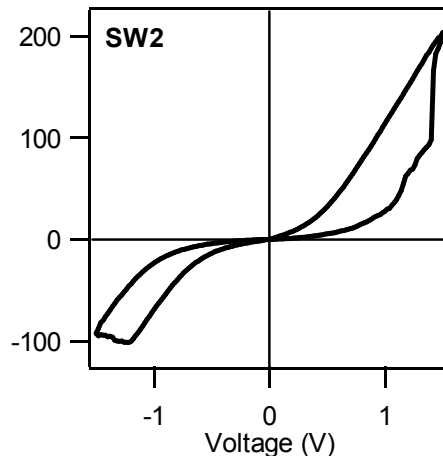
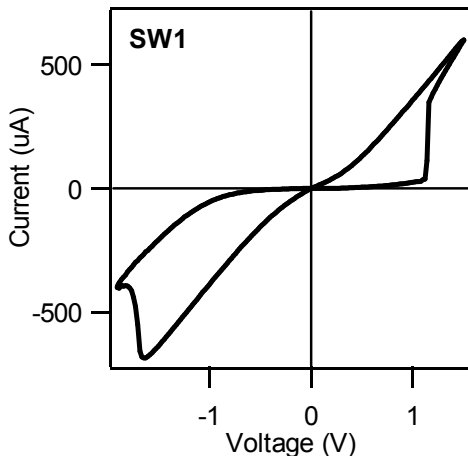
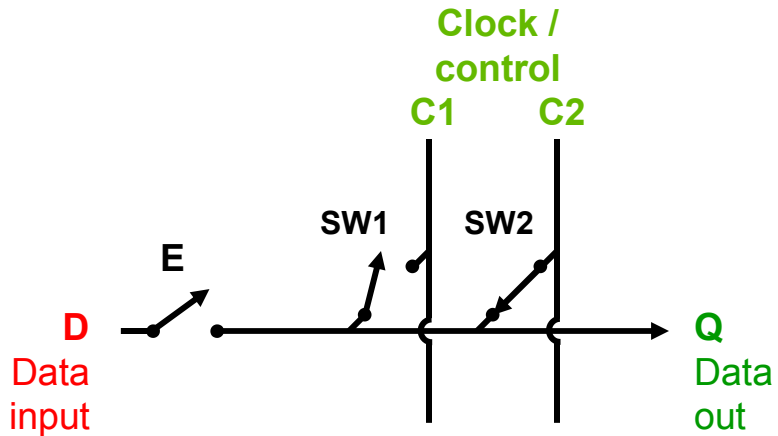
Address lines

Mux/demux

*Mux/demux programming done by E-beam burning

No Gain,
No Logic?

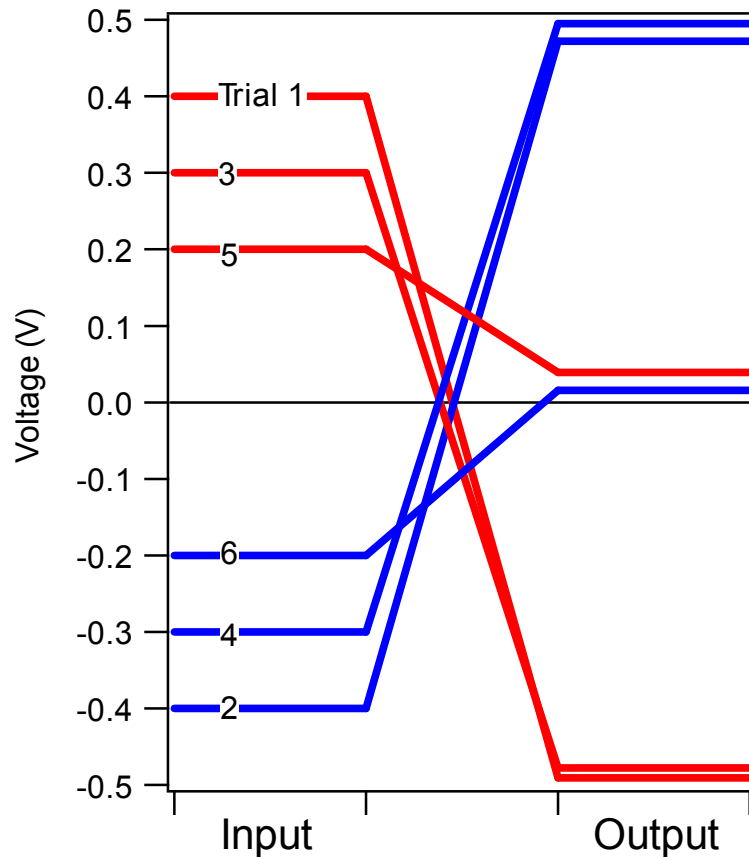
TUNNELING SWITCH LATCH: EXPT DATA



Duncan Stewart



Expt: *Latch works!*



Signal restoration
Inversion, if desired
>100mV operating margin

No nanoscale transistor!

J. Appl. Phys. Feb 1, 2005



The Tunneling-Switch Latch Provides

Logical State Storage

Signal Restoration

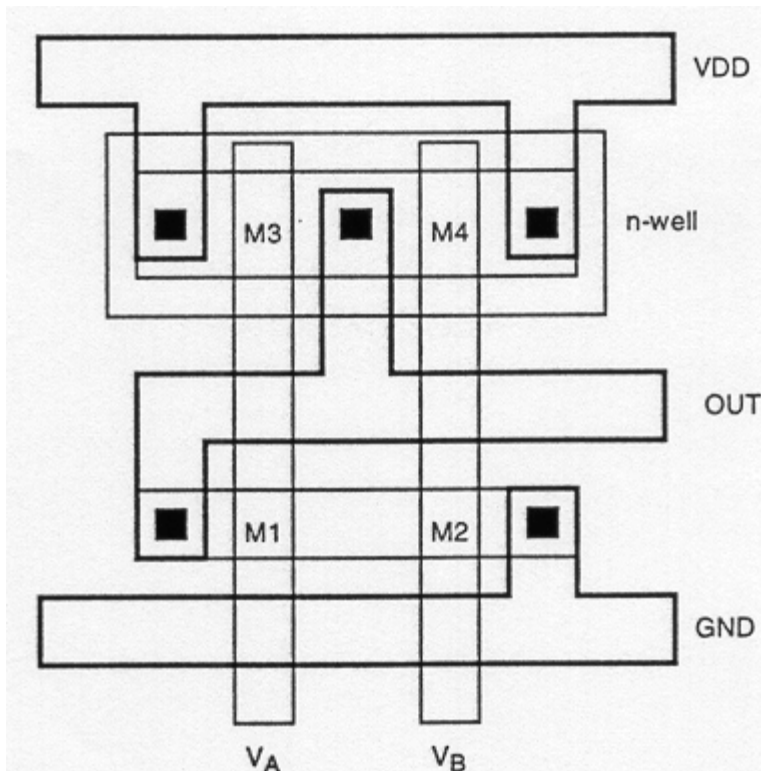
Signal Inversion (Logical NOT)
(with no need for a nanoscale transistor)

Universal Computation!
(Finite State Machine with wired ANDs and ORs)

Area comparison of NAND gates

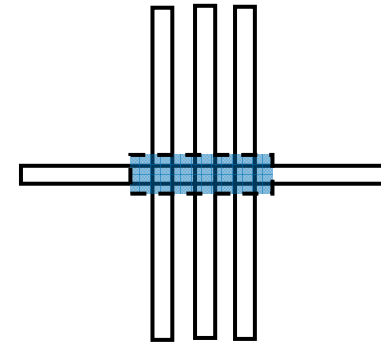


CMOS NAND gate



$$\begin{aligned} \text{Area} &= 36 \times (\text{FP})^2 \\ &= 1.2 \mu^2 @ 90 \text{ nm hp} \end{aligned}$$

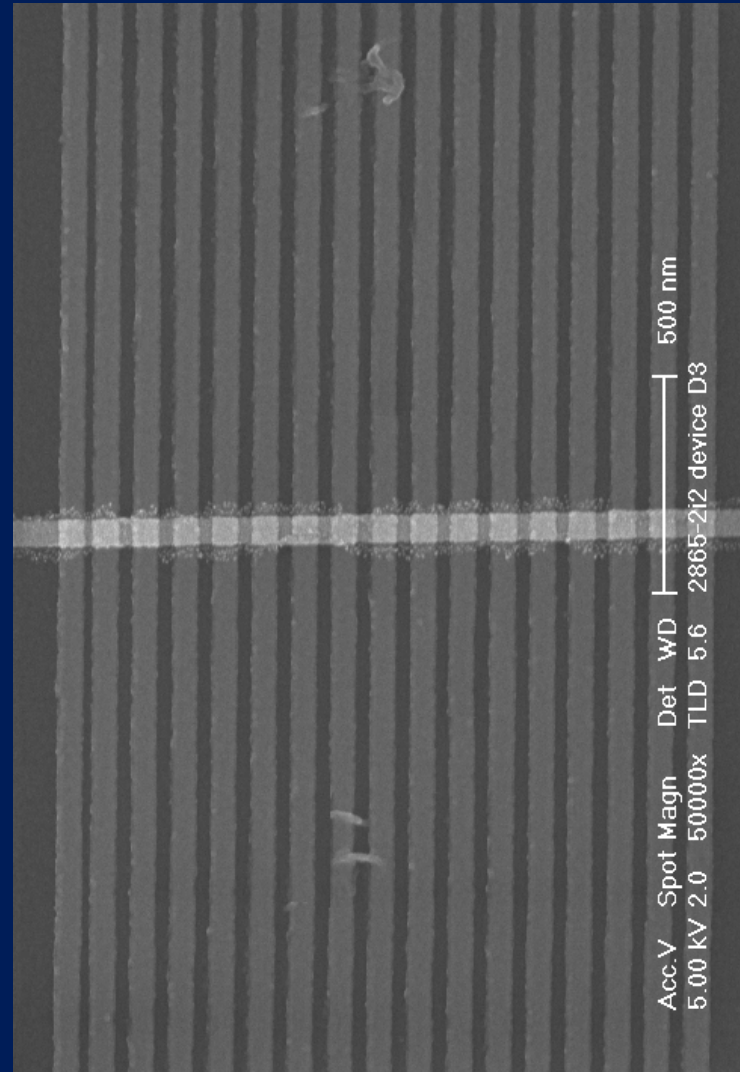
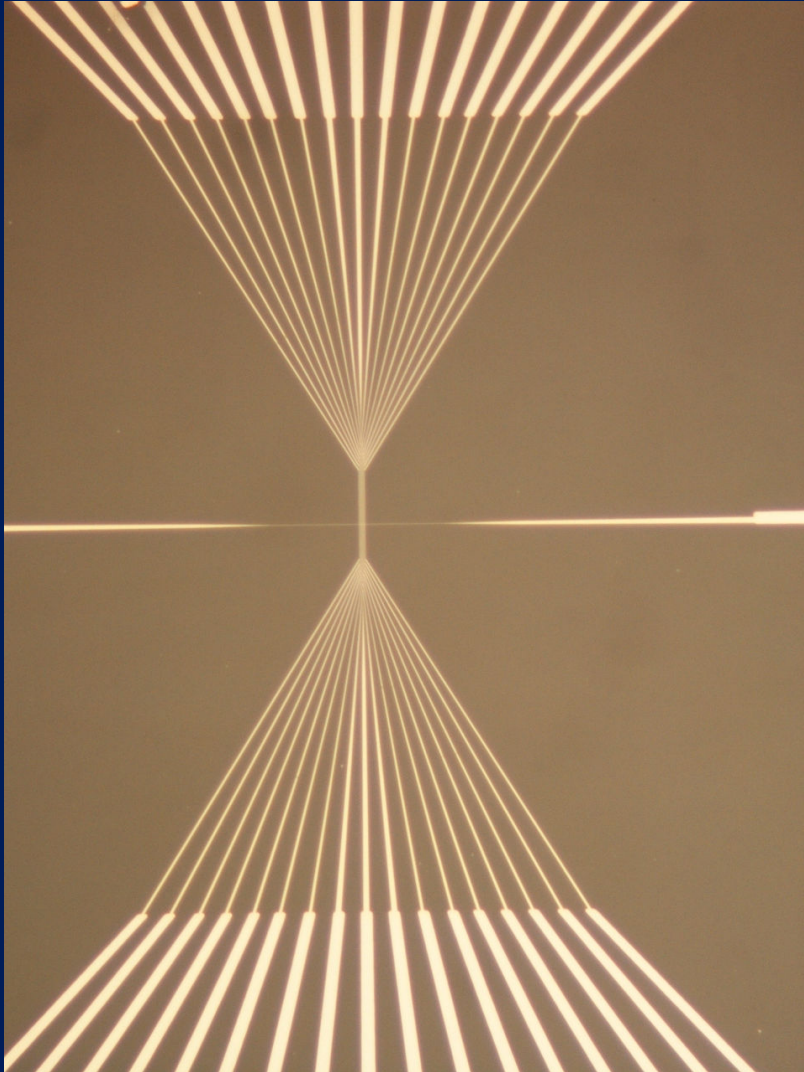
SIMPL NAND gate



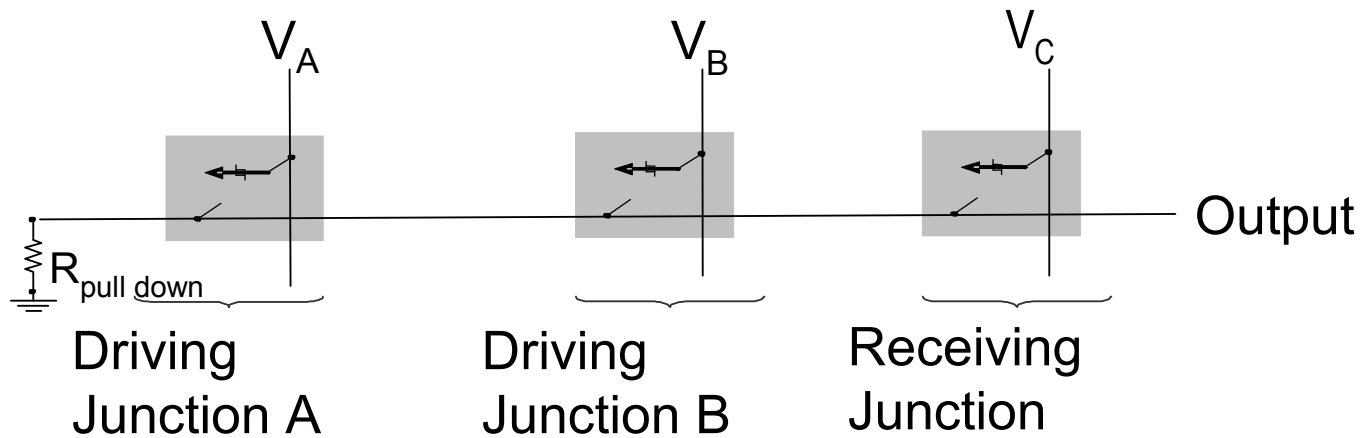
$$\begin{aligned} \text{Area} &= 3 \times (\text{FP})^2 \\ &= 0.01 \mu^2 @ 30 \text{ nm hp} \end{aligned}$$

No V_{DD} , no static power!
Low dynamic power
Register and Logic
Permute inputs and outputs

1 x 17 Latch and Logic Array

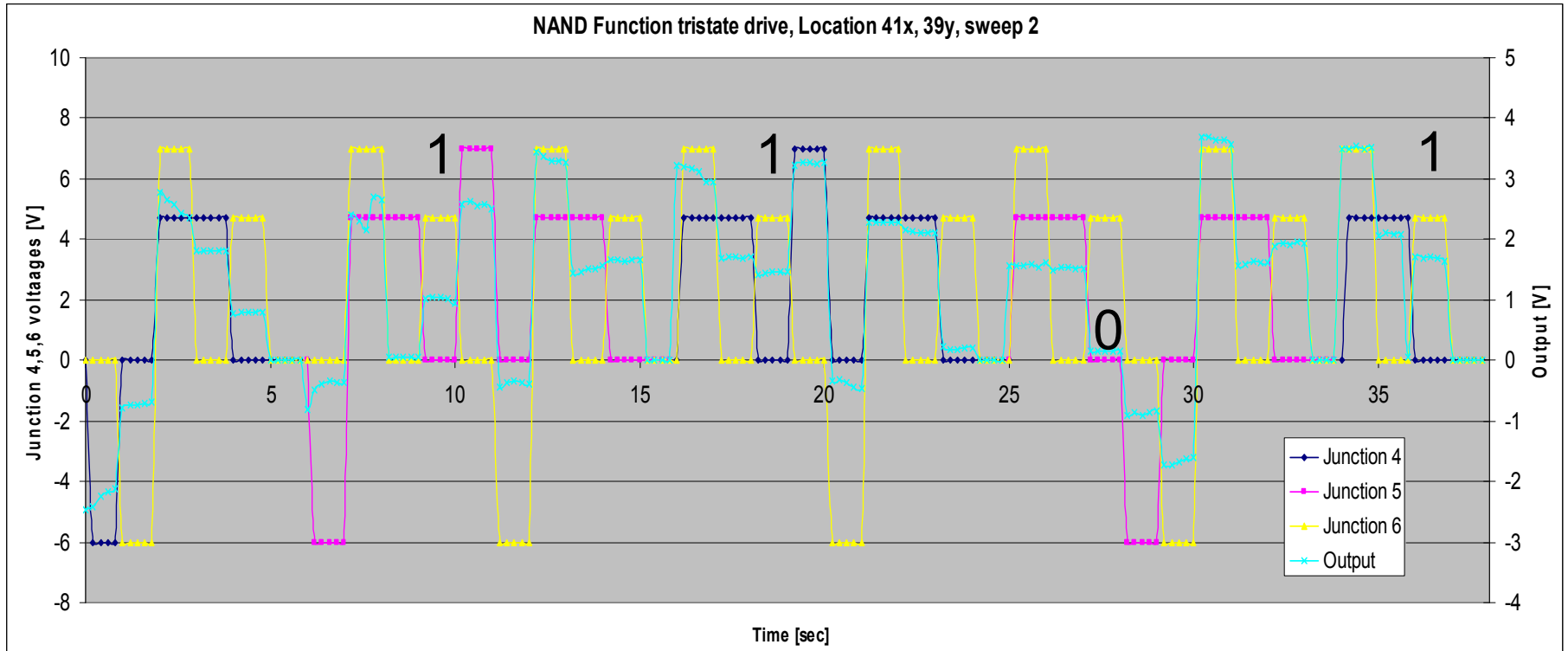


Experimentally measured NAND truth table – Output on $R_{\text{pull down}}$ measured at indicated Step



Junction A	Junction B	$R_{\text{pull down}}$	Step #
0	0	1	10
0	1	1	19
1	1	0	28
1	0	1	37

Experimental V vs. t data for NAND demonstration





Summary of Serial Implication Logic

- SIMPL is simple!
- Tunneling switches → *state machines*.
- Linear array + demux; high density.
- State encoded with impedance, not voltage.
- No static power dissipation.
- Nonvolatile.
- Conditional copy with inversion is 'implication'
- Compiler construction completed.
- nanoCircuits built and currently under test.



i n v e n t